

METHOD OF FABRICATION OF A SUBSTRATE FOR AN EPITAXIAL GROWTH

ABSTRACT

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The present invention relates to a method of fabrication of a substrate for an epitaxial growth. A relaxed epitaxial base layer is obtained on an auxiliary substrate. The invention allows the fabrication of substrates with a more efficient epitaxial growth of a material with a desired lattice parameter on another material with a different lattice
10 parameter. The material can be grown with a high thermodynamic and crystallographic stability. At least a part of the epitaxial base layer is transferred onto a carrier substrate, forming a base substrate, and growing the material of the epitaxial base layer is further grown on the carrier substrate.